

Transistors

High frequency amplifier transistor, RF switching (60V, 50mA)

2SC4774 / 2SC4713K

●Features

- 1) Very low output-on resistance (Ron).
- 2) Low capacitance.

●Absolute maximum ratings (Ta=25°C)

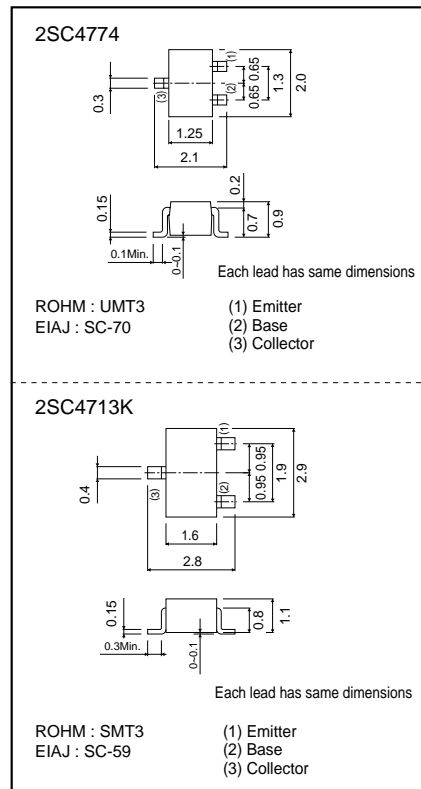
Parameter	Symbol	Limits	Unit
Collector-base voltage	V _{CB0}	12	V
Collector-emitter voltage	V _{CE0}	6	V
Emitter-base voltage	V _{EB0}	3	V
Collector current	I _c	50	mA
Collector power dissipation	2SC4774	0.15	W
	2SC4713K	0.2	
Junction temperature	T _j	150	°C
Storage temperature	T _{stg}	-55~+150	°C

●Packaging specifications and hFE

Type	2SC4774	2SC4713K
Package	UMT3	SMT3
hFE	S	S
Marking	BM*	BM*
Code	T106	T146
Basic ordering unit (pieces)	3000	3000

*Denotes hFE

●External dimensions (Units : mm)



●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV _{CB0}	12	-	-	V	I _c =10μA
Collector-emitter breakdown voltage	BV _{CE0}	6	-	-	V	I _c =1mA
Emitter-base breakdown voltage	BV _{EB0}	3	-	-	V	I _E =10μA
Collector cutoff current	I _{cbo}	-	-	0.5	μA	V _{CB} =10V
Emitter cutoff current	I _{EBO}	-	-	0.5	μA	V _{EB} =2V
Collector-emitter saturation voltage	V _{CE(sat)}	-	-	0.3	V	I _c /I _E =10mA/1mA
DC current transfer ratio	h _{FE}	270	-	560	-	V _{CE} /I _c =10V/10mA
Transition frequency	f _r	300	800	-	MHz	V _{CE} =5V, I _c =10mA
Output capacitance	C _{ob}	-	1	1.7	pF	V _{CB} =10V, I _E =0A, f=1MHz
Output-on resistance	R _{on}	-	2	-	Ω	I _E =3mA, V _I =100mVrms, f=500kHz